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March 2013

# **FQT7N10**

# N-Channel QFET® MOSFET 100 V, 1.7 A, 350 m $\Omega$

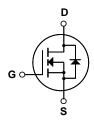
### **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

#### **Features**

- 1.7 A, 100 V,  $R_{DS(on)}$ =350 m $\Omega(Max.)$  @ $V_{GS}$ =10 V,  $I_D$ =0.85 A
- Low Gate Charge (Typ. 5.8 nC)
- Low Crss (Typ. 10 pF)
- 100% Avalanche Tested





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter		FQT7N10	Unit
$V_{DSS}$	Drain-Source Voltage		100	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 70°C)		1.7	А
			1.36	А
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	6.8	А
V <sub>GSS</sub>	Gate-Source Voltage		± 25	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	50	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	1.7	А
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	0.2	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns
$P_D$	Power Dissipation (T <sub>C</sub> = 25°C) - Derate above 25°C		2.0	W
			0.016	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C
'L			300	

### **Thermal Characteristics**

Symbol	Parameter	Тур	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *		62.5	°C/W

<sup>\*</sup> When mounted on the minimum pad size recommended (PCB Mount)

Parameter	Test Conditions	Min	Тур	Max	Unit
aracteristics					
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V
Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to 25	°C	0.1		V/°C
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V			1	μΑ
	V <sub>DS</sub> = 80 V, T <sub>C</sub> = 125°C			10	μА
Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 25 V, V <sub>DS</sub> = 0 V			100	nA
Gate-Body Leakage Current, Reverse	$V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
aracteristics					
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2.0		4.0	V
Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.85 A		0.28	0.35	Ω
Forward Transconductance	$V_{DS} = 40 \text{ V}, I_{D} = 0.85 \text{ A}$ (Note	e 4)	1.85		S
Input Capacitance Output Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz		190 60	250 75	pF pF
Output Capacitance	f = 1.0 MHz		60	75	pF
Reverse Transfer Capacitance			10	13	pF
ing Characteristics					
Turn-On Delay Time	V - 50 V I - 72 A		7	25	ns
Turn-On Rise Time	55		24	60	ns
Turn-Off Delay Time	NG - 20 22		13	35	ns
Turn-Off Fall Time	(Note	4, 5)	19	50	ns
Total Gate Charge	$V_{DS} = 80 \text{ V}, I_{D} = 7.3 \text{ A},$		5.8	7.5	nC
Gate-Source Charge	V <sub>GS</sub> = 10 V		1.4		nC
Gate-Drain Charge	(Note	4, 5)	2.5		nC
				1.7	Α
					A
	1				V
Diam-Source Diode i diward Voltage				1.5	٧
Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{S} = 7.3 \text{ A},$		70		ns
	Breakdown Voltage Breakdown Voltage Temperature Coefficient  Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward Gate-Body Leakage Current, Reverse  Bracteristics Gate Threshold Voltage Static Drain-Source On-Resistance Forward Transconductance  Input Capacitance Output Capacitance Reverse Transfer Capacitance  Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Delay Time Turn-Off Sall Time Total Gate Charge Gate-Drain Charge Gate-Drain Charge  Bource Diode Characteristics ar Maximum Continuous Drain-Source Dio	tracteristics         Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}$ , $I_D = 250 \text{ μA}$ Breakdown Voltage Temperature Coefficient $I_D = 250 \text{ μA}$ , Referenced to 25         Zero Gate Voltage Drain Current $V_{DS} = 100 \text{ V}$ , $V_{GS} = 0 \text{ V}$ VDS = 80 V, $T_C = 125^{\circ}C$ Qate-Body Leakage Current, Forward $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{DS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate Threshold Voltage $V_{DS} = V_{GS}$ , $I_D = 250 \text{ μA}$ Static Drain-Source $V_{DS} = 10 \text{ V}$ , $I_D = 0.85 \text{ A}$ Note On-Resistance $V_{DS} = 40 \text{ V}$ , $I_D = 0.85 \text{ A}$ Input Capacitance $V_{DS} = 25 \text{ V}$ , $V_{CS} = 0 \text{ V}$ , $I_D = 7.3 \text{ A}$ , $I_D = 1.0 \text{ MHz}$ Input Capacitance $V_{DD} = 50 \text{ V}$ , $I_D = 7.3 \text{ A}$ , $I_D = 7.$	Aracteristics       Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}$ , $I_D = 250 \text{ μA}$ 100         Breakdown Voltage Temperature Coefficient $I_D = 250 \text{ μA}$ , Referenced to $25^{\circ}\text{C}$ Zero Gate Voltage Drain Current $V_{DS} = 100 \text{ V}$ , $V_{GS} = 0 \text{ V}$ Gate-Body Leakage Current, Forward $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate Threshold Voltage $V_{DS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate Threshold Voltage $V_{DS} = 40 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate Threshold Voltage $V_{DS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ Gate Characteristics         Value Characteristics and Maximum Ratin	Prain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}, I_D = 250 \text{ μA}$ $100 $ Breakdown Voltage Temperature Coefficient $I_D = 250 \text{ μA}$ , Referenced to $25^{\circ}\text{C}$ $$ 0.1 $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 80 \text{ V}, T_C = 125^{\circ}\text{C}$ $$ $$ Gate-Body Leakage Current, Forward $V_{GS} = 25 \text{ V}, V_{DS} = 0 \text{ V}$ $$ $$ Gate-Body Leakage Current, Reverse $V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$ $$ $$ Brackeristics $V_{CS} = 10 \text{ V}, I_D = 250 \text{ μA}$ $V_{CS} = 25 \text{ V}, V_{DS} = 0 \text{ V}$ $$ $$ $$ Reverse $V_{CS} = 10 \text{ V}, I_D = 250 \text{ μA}$ $V_{CS} = 25 \text{ V}, V_{DS} = 0 \text{ V}$ $$ $$ $$ $$ Reverse $V_{CS} = 10 \text{ V}, I_D = 0.85 \text{ A}$ $$ 0.28 On-Resistance $V_{CS} = 10 \text{ V}, I_D = 0.85 \text{ A}$ $$ 0.28 On-Resistance $V_{CS} = 10 \text{ V}, I_D = 0.85 \text{ A}$ (Note 4) $$ 1.85 Drain-Source Output Capacitance $V_{CS} = 25 \text{ V}, V_{CS} = 0 \text{ V}, I_D = 0.85 \text{ A}$ (Note 4) $$ 1.85 Drain-Source Output Capacitance $V_{CS} = 25 \text{ V}, V_{CS} = 0 \text{ V}, I_D = 0.85 \text{ A}$ (Note 4) $$ 1.85 Drain-Source Drain-Sou	bracteristics         Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}$ , $I_D = 250 \text{ μA}$ $100  - \cdot$ $- \cdot$ Breakdown Voltage Temperature Coefficient $I_D = 250 \text{ μA}$ , Referenced to $25^{\circ}\text{C}$ $- \cdot$ $0.1  - \cdot$ Zero Gate Voltage Drain Current $V_{DS} = 100 \text{ V}$ , $V_{GS} = 0 \text{ V}$ $- \cdot$ $- \cdot$ $100  - \cdot$ Gate-Body Leakage Current, Forward $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ $- \cdot$ $- \cdot$ $100  - \cdot$ Gate-Body Leakage Current, Reverse $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ $- \cdot$ $- \cdot$ $100  - \cdot$ Gate-Body Leakage Current, Reverse $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ $- \cdot$ $- \cdot$ $100  - \cdot$ Gate-Body Leakage Current, Reverse $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ $- \cdot$ $- \cdot$ $100  - \cdot$ Gate-Body Leakage Current, Reverse $V_{GS} = 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$ $- \cdot$ $- \cdot$ $100  - \cdot$ Gate-Body Leakage Current, Reverse $V_{DS} = V_{GS}$ , $I_D = 250 \text{ µA}$ $2.0  - \cdot$ $- \cdot$

- Notes: 
  1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 26mH, I $_{AS}$  = 1.74, V $_{DD}$  = 25V, R $_{G}$  = 25  $\Omega$ , Starting T $_{J}$  = 25°C 3. I $_{SD}$  ≤ 7.3A, di/dt ≤ 300A $_{JLS}$ , V $_{DD}$  ≤ BV $_{DSS}$ , Starting T $_{J}$  = 25°C 4. Pulse Test : Pulse width ≤ 300 $_{JLS}$ , Duty cycle ≤ 2% 5. Essentially independent of operating temperature

## **Typical Characteristics**

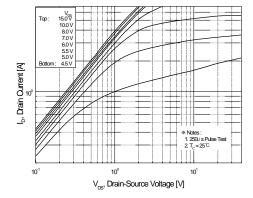


Figure 1. On-Region Characteristics

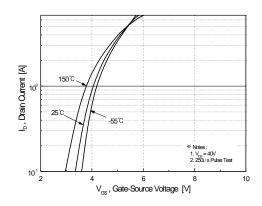


Figure 2. Transfer Characteristics

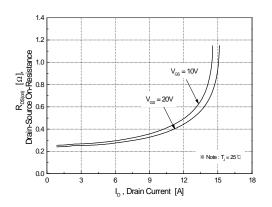


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

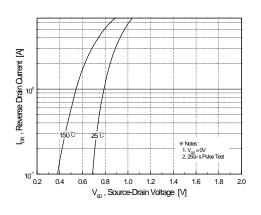


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

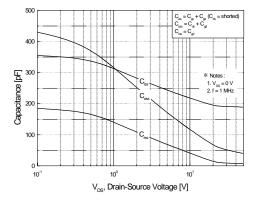


Figure 5. Capacitance Characteristics

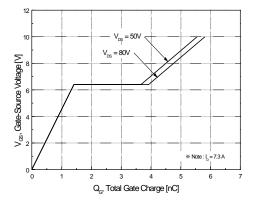
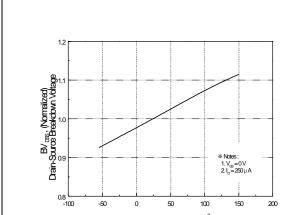


Figure 6. Gate Charge Characteristics



-50

Typical Characteristics (Continued)

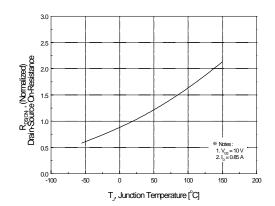
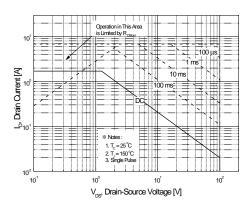


Figure 7. Breakdown Voltage Variation vs. Temperature

T,, Junction Temperature [°C]

150

Figure 8. On-Resistance Variation vs. Temperature



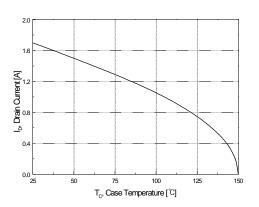


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

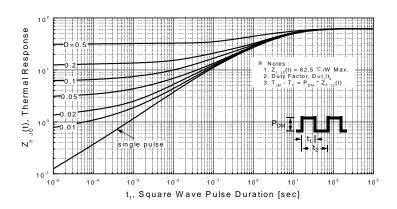
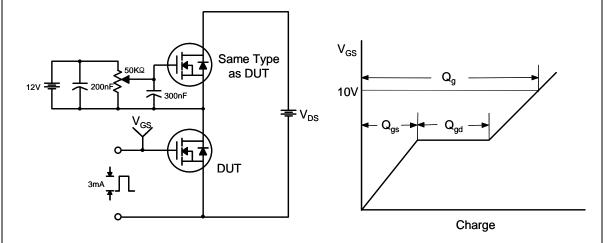
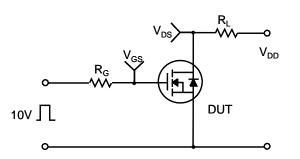


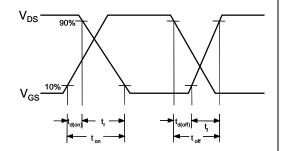
Figure 11. Transient Thermal Response Curve

### **Gate Charge Test Circuit & Waveform**

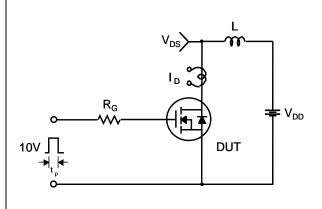


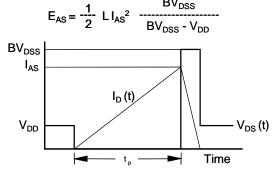
### **Resistive Switching Test Circuit & Waveforms**

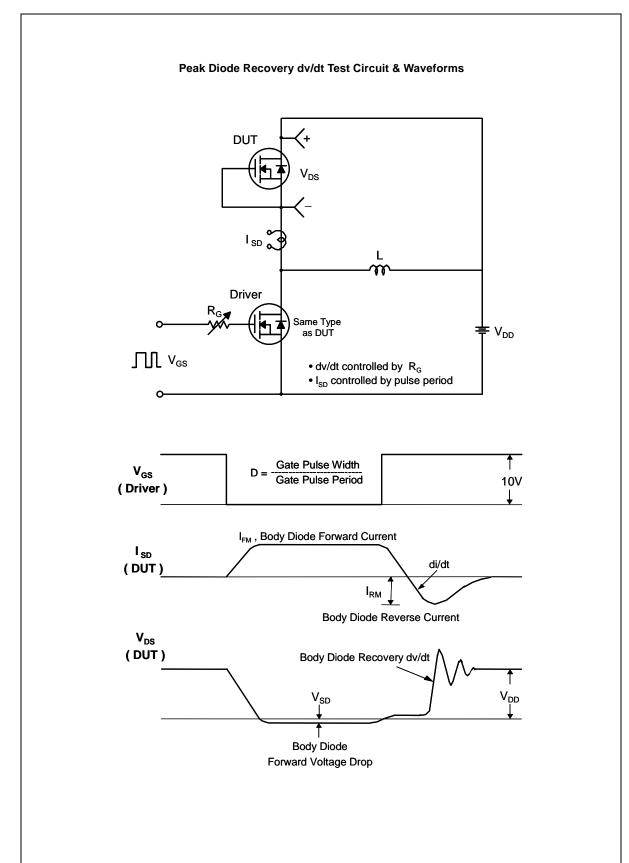


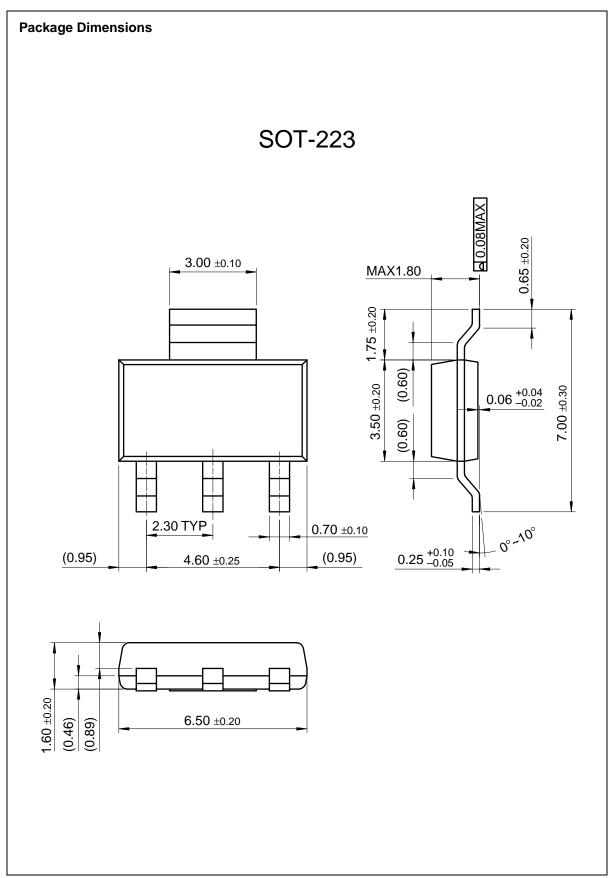


#### **Unclamped Inductive Switching Test Circuit & Waveforms**













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